

FDP6670S/FDB6670S

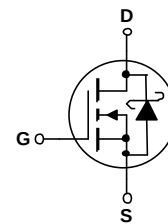
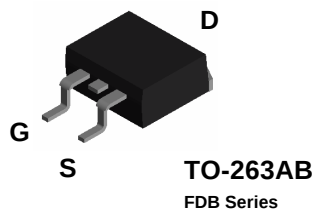
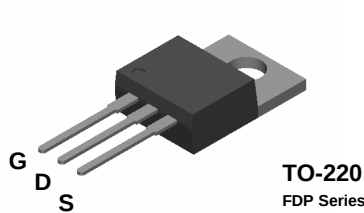
30V N-Channel PowerTrench[®] SyncFET™

General Description

This MOSFET is designed to replace a single MOSFET and parallel Schottky diode in synchronous DC:DC power supplies. This 30V MOSFET is designed to maximize power conversion efficiency, providing a low $R_{DS(ON)}$ and low gate charge. The FDP6670S includes an integrated Schottky diode using Fairchild's monolithic SyncFET technology. The performance of the FDP6670S/FDB6670S as the low-side switch in a synchronous rectifier is indistinguishable from the performance of the FDP6670A/FDB6670A in parallel with a Schottky diode.

Features

- 31 A, 30 V. $R_{DS(ON)} = 8.5 \text{ m}\Omega @ V_{GS} = 10 \text{ V}$
 $R_{DS(ON)} = 12.5 \text{ m}\Omega @ V_{GS} = 4.5 \text{ V}$
- Includes SyncFET Schottky body diode
- Low gate charge (23nC typical)
- High performance trench technology for extremely low $R_{DS(ON)}$ and fast switching
- High power and current handling capability



Absolute Maximum Ratings

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain-Source Voltage	30	V
V_{GSS}	Gate-Source Voltage	± 20	V
I_D	Drain Current – Continuous (Note 1)	62	A
	– Pulsed (Note 1)	150	
P_D	Total Power Dissipation @ $T_C = 25^\circ\text{C}$	62.5	W
	Derate above 25°C	0.5	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to $+150$	$^\circ\text{C}$
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	275	$^\circ\text{C}$

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	2.1	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	$^\circ\text{C/W}$

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
FDB6670S	FDB6670S	13"	24mm	800 units
FDP6670S	FDP6670S	Tube	n/a	45

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Drain-Source Avalanche Ratings (Note 1)						
W_{DSS}	Single Pulse Drain-Source Avalanche Energy	$V_{DD} = 25\text{ V}, \quad I_D = 16.5\text{ A}$			285	mJ
I_{AR}	Maximum Drain-Source Avalanche Current				16.5	A
Off Characteristics						
BV_{DSS}	Drain–Source Breakdown Voltage	$V_{GS} = 0\text{ V}, \quad I_D = 1\text{mA}$	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 26\text{mA}$, Referenced to 25°C		24		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 24\text{ V}, \quad V_{GS} = 0\text{ V}$			500	μA
I_{GSSF}	Gate–Body Leakage, Forward	$V_{GS} = 20\text{ V}, \quad V_{DS} = 0\text{ V}$			100	nA
I_{GSSR}	Gate–Body Leakage, Reverse	$V_{GS} = -20\text{ V}, \quad V_{DS} = 0\text{ V}$			–100	nA
On Characteristics (Note 2)						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, \quad I_D = 1\text{mA}$	1	2.2	3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 26\text{mA}$, Referenced to 25°C		–4.5		mV/°C
$R_{DS(on)}$	Static Drain–Source On–Resistance	$V_{GS} = 10\text{ V}, \quad I_D = 31\text{ A}$ $V_{GS} = 4.5\text{ V}, \quad I_D = 26.5\text{ A}$ $V_{GS}=10\text{ V}, I_D =31\text{ A}, T_J=125^\circ\text{C}$		5 8 10	8.5 12.5 19	mΩ
$I_{D(on)}$	On–State Drain Current	$V_{GS} = 10\text{ V}, \quad V_{DS} = 10\text{ V}$	60			A
g_{FS}	Forward Transconductance	$V_{DS} = 10\text{ V}, \quad I_D = 31\text{ A}$		69		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS} = 15\text{ V}, \quad V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$		2639		pF
C_{oss}	Output Capacitance			737		pF
C_{rss}	Reverse Transfer Capacitance			222		pF
Switching Characteristics (Note 2)						
$t_{d(on)}$	Turn–On Delay Time	$V_{DS} = 15\text{ V}, \quad I_D = 1\text{ A},$ $V_{GS} = 10\text{ V}, \quad R_{GEN} = 6\text{ }\Omega$		13	24	ns
t_r	Turn–On Rise Time			10	21	ns
$t_{d(off)}$	Turn–Off Delay Time			39	62	ns
t_f	Turn–Off Fall Time			35	56	ns
Q_g	Total Gate Charge	$V_{DS} = 15\text{ V}, \quad I_D = 31\text{ A},$ $V_{GS} = 5\text{ V}$		23	32	nC
Q_{gs}	Gate–Source Charge			9		nC
Q_{gd}	Gate–Drain Charge			8		nC
Drain–Source Diode Characteristics						
V_{SD}	Drain–Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, \quad I_S = 3.5\text{ A}$ (Note 1) $V_{GS} = 0\text{ V}, \quad I_S = 7\text{ A}$ (Note 1)		0.39 0.48	0.7 0.9	V
t_{rr}	Diode Reverse Recovery Time	$I_F = 3.5\text{ A},$ $dI_F/dt = 300\text{ A}/\mu\text{s}$ (Note 2)		32		nS
Q_{rr}	Diode Reverse Recovery Charge			56		nC

Notes:

1. Pulse Test: Pulse Width < 300 μs , Duty Cycle < 2.0%
2. See "SyncFET Schottky body diode characteristics" below.

Typical Characteristics

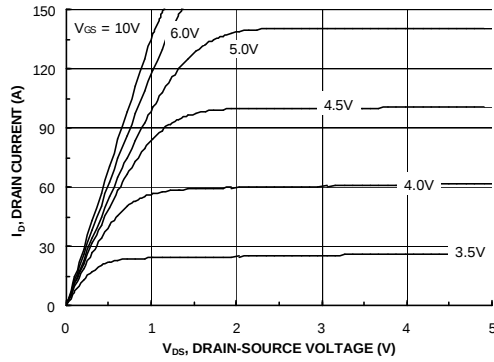


Figure 1. On-Region Characteristics.

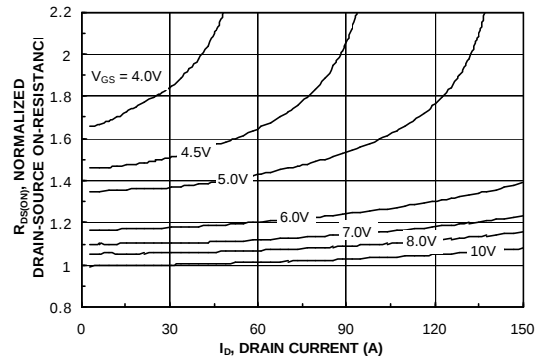


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

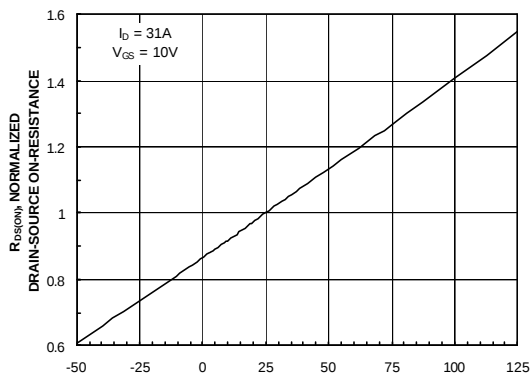


Figure 3. On-Resistance Variation with Temperature.

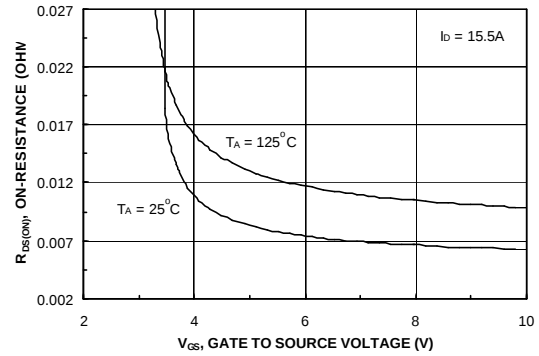


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

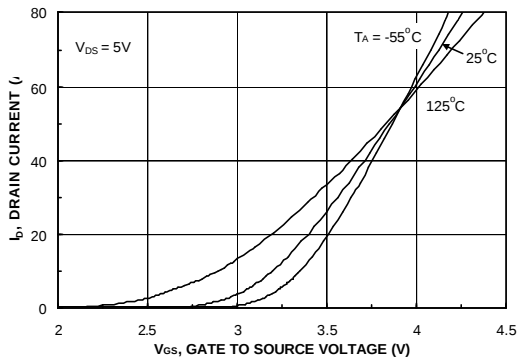


Figure 5. Transfer Characteristics.

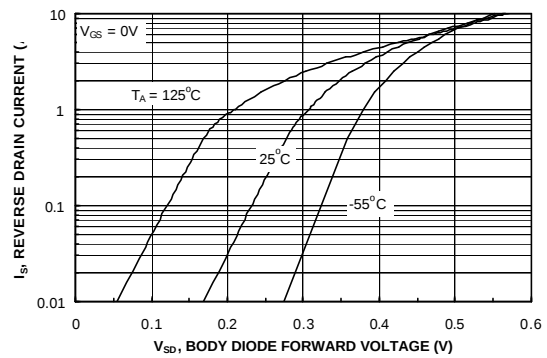


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics (continued)

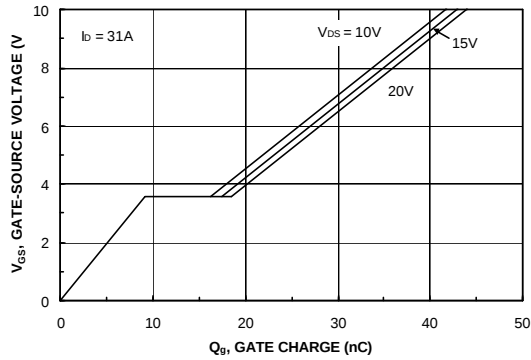


Figure 7. Gate Charge Characteristics.

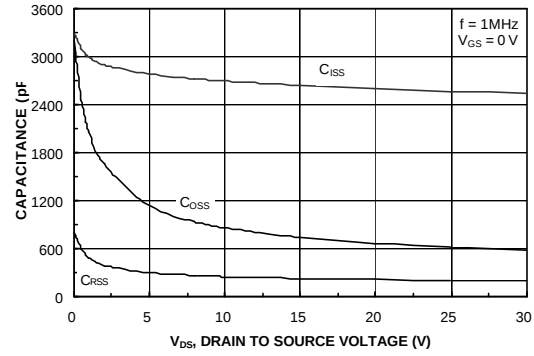


Figure 8. Capacitance Characteristics.

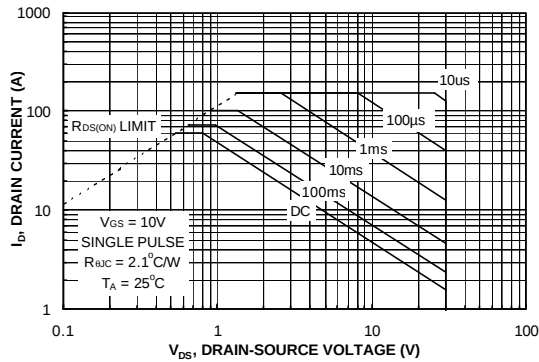


Figure 9. Maximum Safe Operating Area.

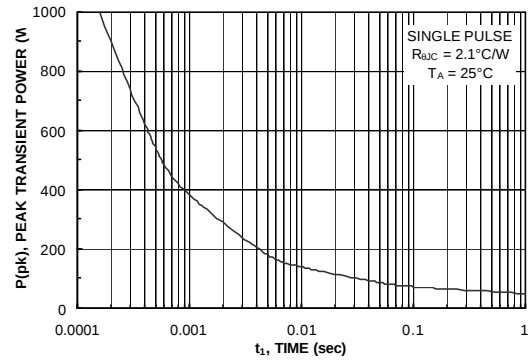


Figure 10. Single Pulse Maximum Power Dissipation.

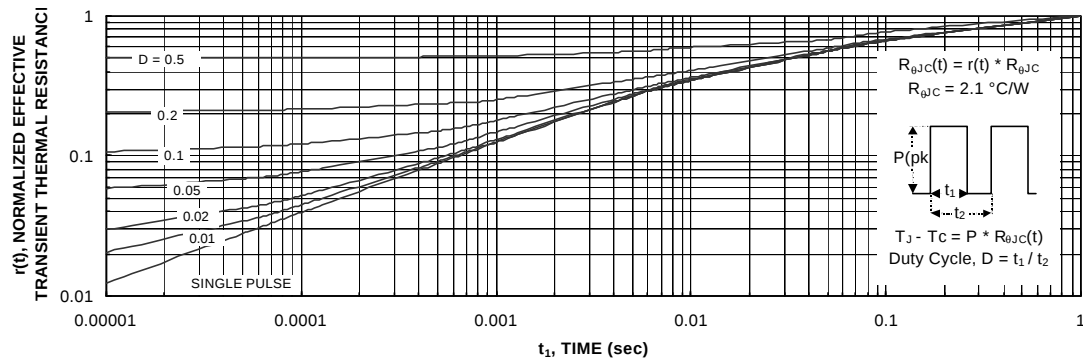


Figure 11. Transient Thermal Response Curve.

Typical Characteristics (continued)

SyncFET Schottky Body Diode Characteristics

Fairchild's SyncFET process embeds a Schottky diode in parallel with PowerTrench MOSFET. This diode exhibits similar characteristics to a discrete external Schottky diode in parallel with a MOSFET. Figure 12 FDP6670S.

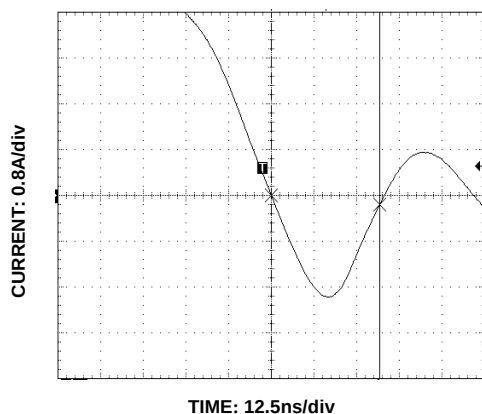


Figure 12. FDP6670S SyncFET body diode reverse recovery characteristic.

For comparison purposes, Figure 13 shows the reverse recovery characteristics of the body diode of an equivalent size MOSFET produced without SyncFET (FDP6670A).

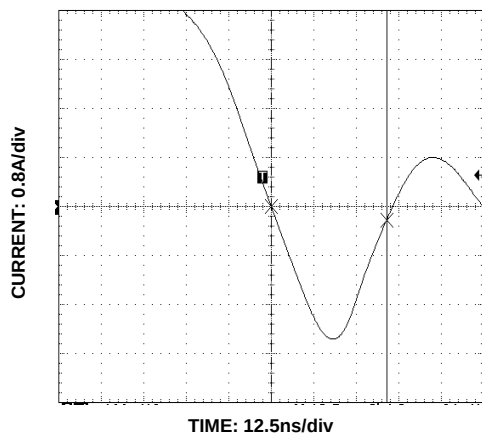
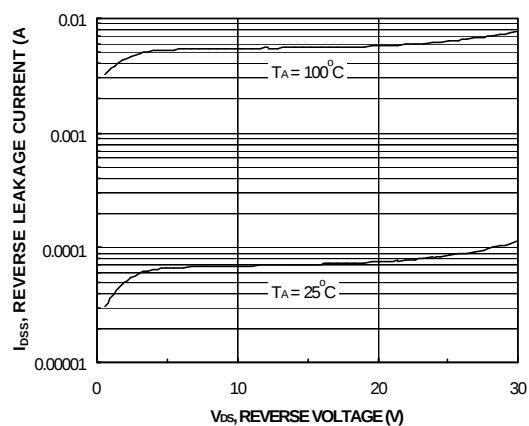


Figure 13. Non-SyncFET (FDP6670A) body diode reverse recovery characteristic.

Schottky barrier diodes exhibit significant leakage at high temperature and high reverse voltage. This will increase the power in the device.

Figure 14. SyncFET diode reverse leakage versus drain-source voltage and temperature.



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